PMEG2010ER

1 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 29 December 2008

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 20 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{F(AV)}$	average forward current	square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$				
		T _{amb} ≤ 130 °C	<u>[1]</u> -	-	1	Α
		T _{sp} ≤ 145 °C	-	-	1	Α
V_R	reverse voltage		-	-	20	V
V_{F}	forward voltage	I _F = 1 A	-	310	340	mV
I _R	reverse current	$V_R = 20 \text{ V}$	-	250	1000	μΑ

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. 64 -
2	anode	1 2	1 - 2
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package	ackage			
	Name	Description	Version		
PMEG2010ER	-	plastic surface-mounted package; 2 leads	SOD123W		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2010ER	B5

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C	-	20	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$			
		$T_{amb} \le 130 ^{\circ}C$	<u>[1]</u> -	1	Α
		$T_{sp} \le 145 ^{\circ}C$	-	1	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] _	50	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	0.57	W
			[3][5]	0.95	W
			[3][1]	1.8	W

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

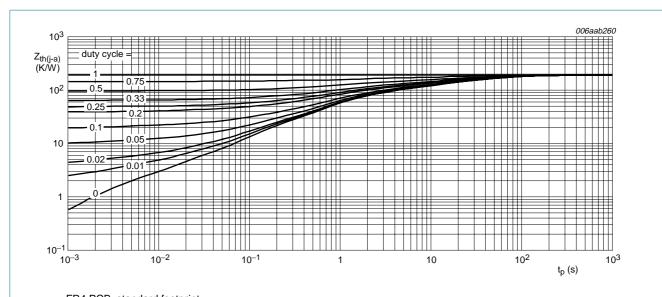
- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] $T_i = 25$ °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

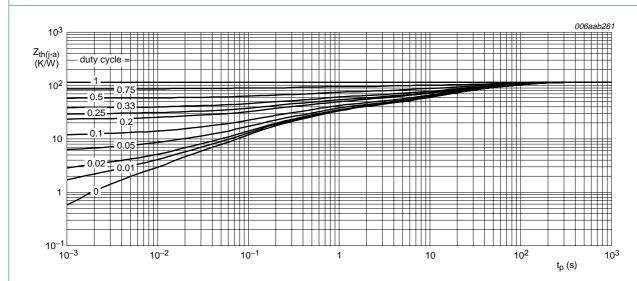
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ιι() α)	thermal resistance from	in free air	[1][2]			
	junction to ambient		<u>[3]</u> _	-	220	K/W
			<u>[4]</u> _	-	130	K/W
			[5] _	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	18	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Soldering point of cathode tab.



FR4 PCB, standard footprint

Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

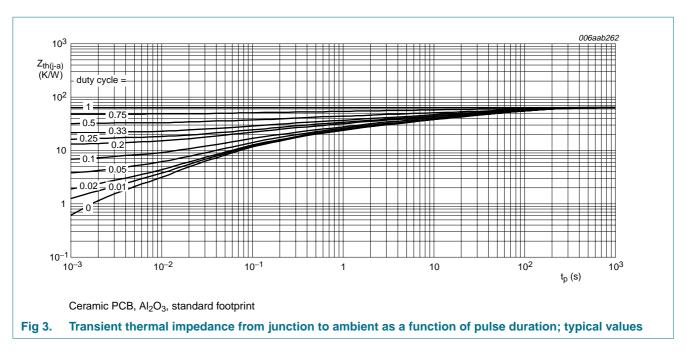


FR4 PCB, mounting pad for cathode 1 cm²

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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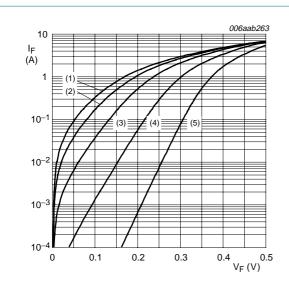


7. Characteristics

 Table 7.
 Characteristics

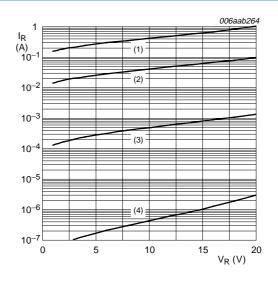
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 0.1 A$	-	220	250	mV
		$I_F = 0.7 A$	-	290	320	mV
		I _F = 1 A	-	310	340	mV
I _R	reverse current	$V_R = 5 V$	-	60	-	μΑ
		V _R = 20 V	-	250	1000	μΑ
C _d	diode capacitance	f = 1 MHz				
		V _R = 1 V	-	175	-	pF
		V _R = 10 V	-	65	-	pF



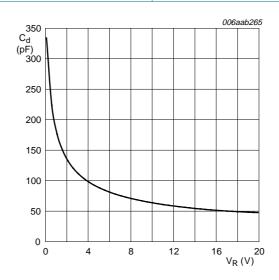
- (1) $T_i = 150 \,^{\circ}\text{C}$
- (2) $T_i = 125 \, ^{\circ}C$
- (3) $T_i = 85 \, ^{\circ}C$
- (4) $T_j = 25 \,^{\circ}C$
- (5) $T_i = -40 \, ^{\circ}C$

Fig 4. Forward current as a function of forward voltage; typical values



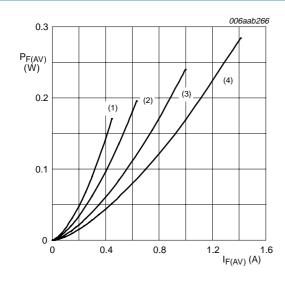
- (1) T_j = 125 °C
- (2) $T_j = 85 \, ^{\circ}C$
- (3) $T_j = 25 \,^{\circ}C$
- (4) $T_j = -40 \, ^{\circ}C$

Fig 5. Reverse current as a function of reverse voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

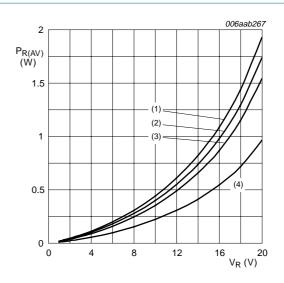
Diode capacitance as a function of reverse voltage; typical values Fig 6.



T_j = 150 °C

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

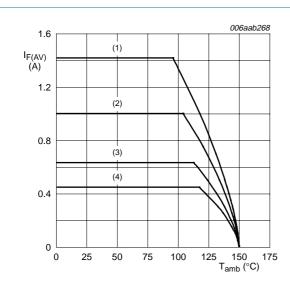
Fig 7. Average forward power dissipation as a function of average forward current; typical values



T_i = 125 °C

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

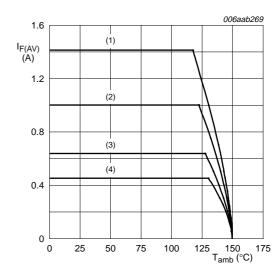
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

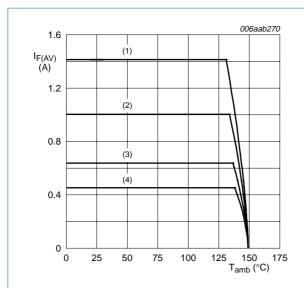
- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values

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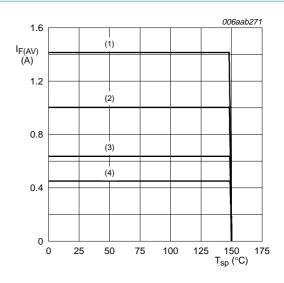
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Ceramic PCB, Al₂O₃, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

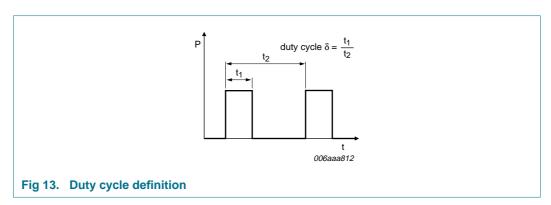
Fig 11. Average forward current as a function of ambient temperature; typical values



- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

8. Test information

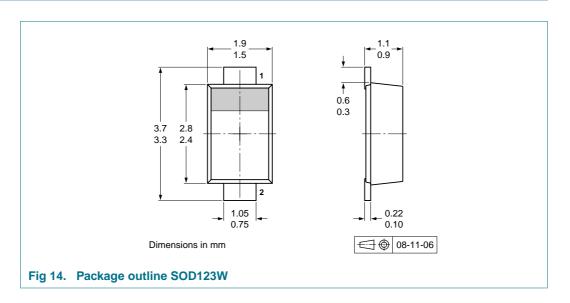


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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10. Packing information

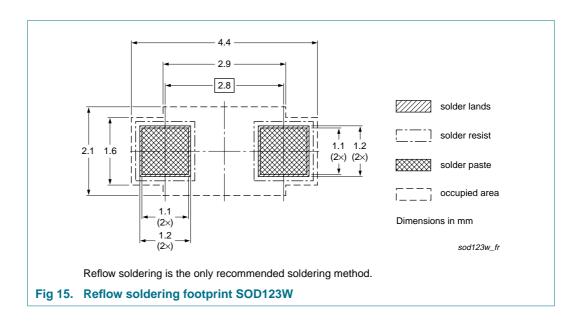
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG2010ER	SOD123W	4 mm pitch, 8 mm tape and reel	-115

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering





12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2010ER_1	20081229	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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